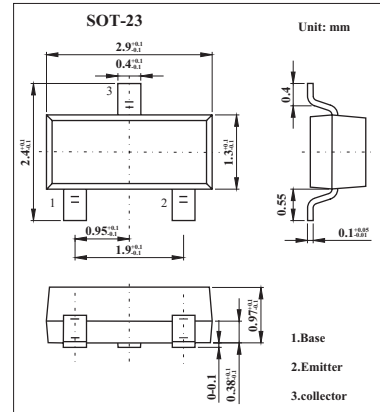


**2SD2226K**

■ Features

- High DC current gain.
- High emitter-base voltage.
- Low saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	60	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	12	V
Collector current	I <sub>c</sub>	0.15	A
		0.2 *	
Collector power dissipation	P <sub>c</sub>	0.2	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* Single pulse Pw=100ms.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV <sub>CB0</sub>	I <sub>c</sub> =10μA	60			V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>c</sub> =1mA	50			V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10μA	12			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =50V			0.3	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> =12V			0.3	μA
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> /I <sub>B</sub> =50mA/5mA			0.3	V
DC current transfer ratio *	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =1mA	820		2700	
Output capacitance *	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>E</sub> = -10mA, f=100MHz		250		MHz
Transition frequency	C <sub>ob</sub>	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz		3.5		pF

\* Measured using pulse current.

■ hFE Classification

Marking	BJ	
	V	W
hFE	820~1800	1200~2700